RAM ENTERPRISE

THE POWER SOLUTIONS



MICRO-MASTER-FRC

IGBT-MOSFET DRIVER Excellent Plug & Play solution!!

Features

Advanced version of Micro-FRC model

- 1W Compact Dual channel driver
- ➤ Switching frequency up to 50 KHz
- 🟲 ±6A gate current, +15V/-10V
- ➤ Drive up to 1200V IGBT Module
- ➤ Electrical Interface
- Advance active clamping
- Integrated short-circuit soft shutdown

- Gate clamping
- Individual Rg ON & Rg OFF Resistor
 - Less aging effect due to ASIC
 - Primary/Sec. under voltage lockout
 - Vce monitoring for short circuit current
 - Superior EMI-EMC
 - Easy tuning with various IGBT module In-built Dead-band Control

Benefits

- ➤ On board isolated DC-DC converter No need of separate SMPS.
- ▶ Interface for 13V...15 V logic level Direct compatible with any Controller.
- **Common fault feedback signal to interface with controller Avoid Extra component.**

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- Field configurable blocking time Flexibility in your hand, use any make IGBT !!
- Safe isolation to IEC 61800-5-1, IEC-60664-1 & En50178, protection class II

Grid Supply

User Selectable Rg

Application









CORONA TRETAR



MEDICAL-X RAY

INDUCTION EQUIPMENT

"Drive the IGBT with experience hand"

Batlery

SOLAR INVERTER

Home Power/

Appliances

UPS

WEB: www.ramenterprise.co.in



Technical Specification

Recommended Operating condition

| Power Supply & Monitoring MIN TYP MAX |
|---|
| 1. Supply Voltage Vcc to GND : 14.5 15 16 V |
| 2. Supply Current Icc (Without Load): 100 mA (@49KHz PWM I/P) |
| 3. Under Voltage Primary, Set Fault : 11.3 12.0 12.7 V |
| Clear Fault : 11.9 12.6 13.3 V |
| Secondary, Set Fault : 11.5 12.0 12.5 V |
| Clear Fault : 12.1 12.6 13.1 V |

Logical Inputs & Outputs

| 1. Input Bias Current | : 190 µA |
|-----------------------------------|-------------------------------------|
| 2. Interface Logic level | : 12 V 15.0 V logic level |
| 3. Turn-on threshold | : 12 V |
| 4. Turn off threshold | : 10.7 V |
| 5. SOx output , failure Condition | : 0.7 V Max., I (SOx) < 20 mA total |

Short-Circuit Protecti

| ion | . Diode sense method |
|--------|--------------------------|
| eshold | : 9.3 V (Internally Fix) |

1. Vce-monitoring threshold Trip adjustment D10,D12 2. Factory Set response time 3. Minimum response time

: 1W ZENER / UF4007 / MUR1100 : 4.5 µSec (C5,C6:150pF) : 4.5 µSec

- 4. Available blocking time (R7)
- 5. Minimum blocking time (R7)

: 49 mSec (User Selectable 100K) : 9 µSec(0E)

Timing Characteristic (Input to Output of Driver board under No-Load)

| 1. Turn-on delay t _{d(on)} | : 1 uS, Max. | | | |
|---------------------------------------|----------------|--|---|--|
| 2. Turn-off delay t _{d(off)} | : 1.2 uS, Max. | | | |
| 3. Dead band Factory Set | : 4.0 uS, Max. | | | |
| | <pre>c</pre> | | 1 | |

For detail timing information of driver core, refer part specific datasheet.

Protection Available on driver board

- 1. Primary/Secondary Under voltage monitoring & error feedback.
- 2. Power supply reverse polarity.
- 3. Soft Shut down, For IGBT Over Voltage.
- 4. Vce monitoring for short circuit current.
- 5. Schmitt trigger at the Input stage, highly susceptible to noise. 6. IGBT Gate clamping.

Electrical Isolation

| Test voltage (50 Hz/1 sec) | |
|--------------------------------|----------|
| 1. Primary to secondary side | : 4.0 KV |
| 2. Secondary to secondary side | : 4.0 KV |

This gate driver is suited for HiPot testing. Nevertheless, it is strongly J2 Pin Detail: recommended to limit the testing time to 1s slots. Excessive HiPot testing at $\ensuremath{^1}$ voltages much higher than 850V_{AC(eff)} may lead to insulation degradation. No 3,4 degradation has been observed over 1 min. testing at 2500V_{AC(eff)} Each driver core production sample shipped has undergone 100% testing at the given value or higher for 1s.

: 2SC0106T2A1-12 from Power Integration

Output Voltage / Current / Power

| 1. Turn-on voltage, V _{GHx} | : 15.0 V, any load condition |
|---------------------------------------|-----------------------------------|
| 2. Turn-off voltage, V _{GLx} | : -9.9 V, No load |
| 3. Turn-off voltage, V _{GLx} | :-8.0 V@1W |
| 4. Gate Peak Current I_{out} | : ±6 Amp |
| 5. Internal Gate resistance | : 0.5 Ω |
| 6. External Gate resistance | : Minimum 2.5 Ω, <25kHz |
| | : Minimum 5 Ω, >25kHz |
| 7. Switching frequency F | : 50 Khz |
| 8. Output Power | : 1.0 W, T _{amb} <85 °C |
| | : 1.2 W , T _{amb} <70 °C |
| | : 0.35W, T _{amb} <105 °C |

Part used on Plug & play driver

THE POWER SOLUTIONS

Environmental

Working temperature Storage temperature

: -40 to 105 °C : -40 to 90 °C

: ANY MAKE

Driving Capability

All usual IGBT modules up to 600 A /1200 V or 600A/600V. Driving power depends on switching frequency so in case of any doubt during selection process pl. contact us.

Interfacing with Control Circuit

1. Electrical ERROR : Low to High / High to Low (Site selectable)

LED Indication Power ON: Green (Normally ON, Off during Power supply fault) ERROR : RED (ON during Under Voltage / DESAT/ IGBT Fault)

ORDERING CODE - 220221008



Interfacing with Control Circuit

14-PIN FRC Pin Detail:

| L,5,7,13,14 | N.C. | | | |
|-------------|-------|----------|-----------|--|
| 2 | PWM B | 4 | PWMA | |
| 3 | ERROR | 6 | EXT RESET | |
| 3,9 | +15V | 10,11,12 | GND | |

NOTE: EXT RESET must be GND, if not interface with Controller.

Interfacing with IGBT

J1 Pin Detail:

- CB- Collector for bottom IGBT switch (High Voltage)
- 2 NC

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- 3,4 GB-GATE for bottom IGBT Switch
- 5 EB - Emitter for bottom IGBT Switch

- CT- Collector for top IGBT switch (High Voltage)
- NC
- GT-GATE for top IGBT Switch
- ET Emitter for top IGBT Switch

MECHANICAL DIMENSION:



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